

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
3 February 2005 (03.02.2005)

PCT

(10) International Publication Number  
**WO 2005/010996 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 29/739**

(21) International Application Number:

PCT/JP2004/008516

(22) International Filing Date: 10 June 2004 (10.06.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

2003-195498

11 July 2003 (11.07.2003) JP

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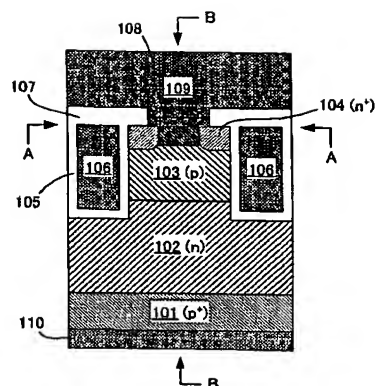
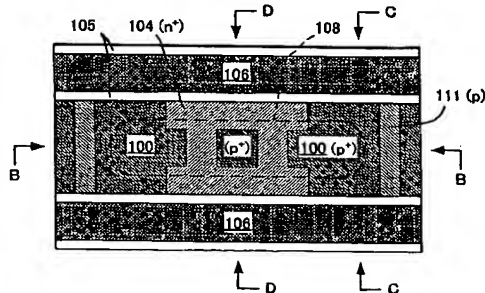
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,

[Continued on next page]

(54) Title: SEMICONDUCTOR DEVICE



(57) Abstract: To present a semiconductor device capable of operating stably even at large current, by lessening current concentration into the corners of contact opening after switching off and suppressing local heat generation without raising the ON voltage. In an insulated gate transistor divided by P field region 111 and gate electrode 106, having N<sup>+</sup> emitter region 104 and P<sup>+</sup> emitter region 100, and controlling conduction between emitter and collector by voltage applied to gate electrode 106, the shape of contact opening 108 contacting emitter (N<sup>+</sup> emitter region 104 and P<sup>+</sup> emitter region 100) and emitter electrode is formed of curved lines at four corners. Hence, eliminating right-angle apex, hole current from the field region into the emitter electrode after switching off is prevented from concentrating at one point.



SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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**Published:**

- *with international search report*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*